

S3AB-S3MB

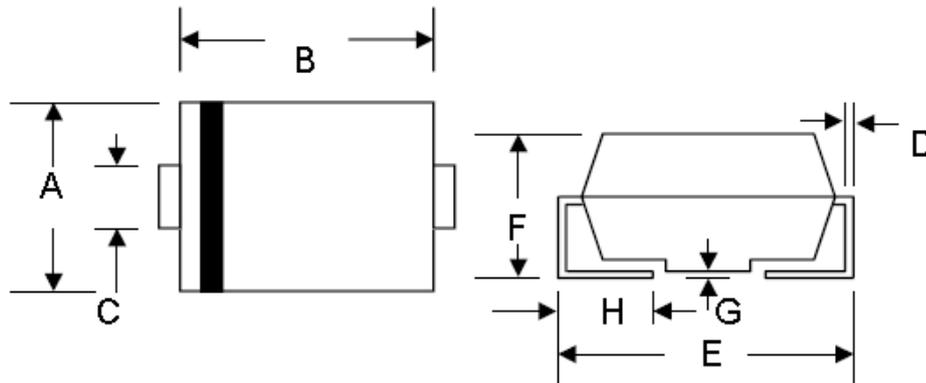
3.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER

Features:

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data:

- Case: molded plastic
- Terminals: Plated leads, solderable per MIL-STD-750, Method 2026
- Polarity: Cathode band or Cathode Notch
- Weight:0.093 grams(approx)

Mechanical Dimensions:


SMB/DO-214AA				
Dim.	Min.	Max.	Min.	Max.
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.91	2.11	0.075	0.083
D	0.152	0.305	0.006	0.012
E	5.08	5.59	0.200	0.220
F	2.13	2.44	0.084	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.029	0.05
	In mm		In inch	

SMB

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Marking Diagram:


Where XXXXX is YYWWL

S3AB	= Part Name
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
S3AB-S3MB	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	S3AB	S3BB	S3DB	S3GB	S3JB	S3KB	S3MB	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Average forward rectified output current @ $T_L = 75^\circ\text{C}$	I_O	3.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	100							A
Forward Voltage @ $I_F = 3.0\text{A}$	V_{FM}	1.20							V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$	I_{RM}	5.0 250							μA
Reverse recovery time (Note 1)	t_{rr}	2.5							ns
Typical Junction Capacitance (Note 2)	C_J	60							pF
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$	13							K/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150							$^\circ\text{C}$

Note: 1. Reverse recovery condition $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{rr}=0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. Mounted on P.C. Board with 8.0mm² land area.

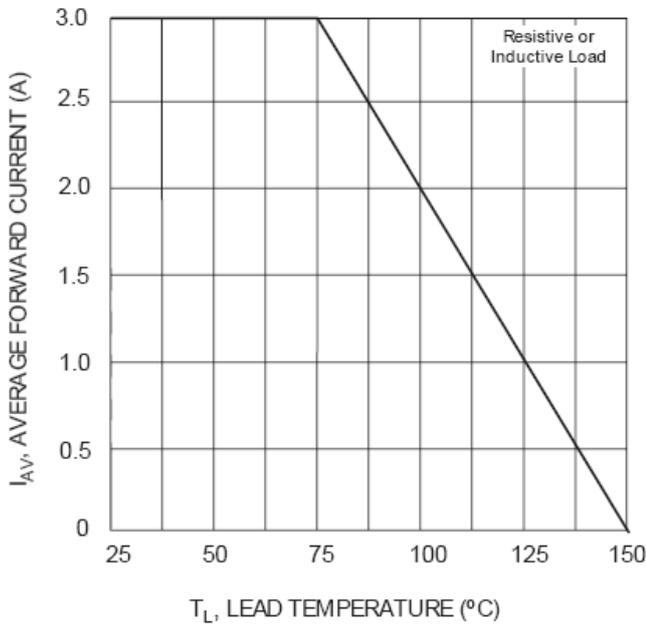


Fig. 1 Forward Current Derating Curve

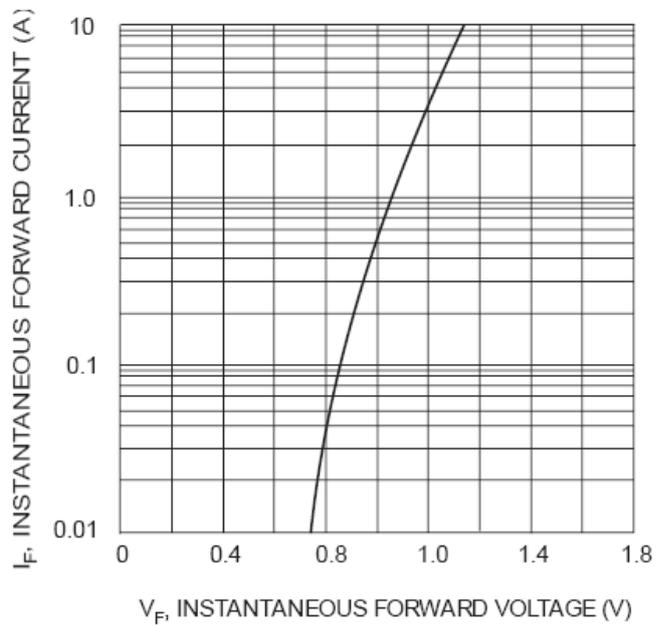


Fig. 2 Typical Forward Characteristics

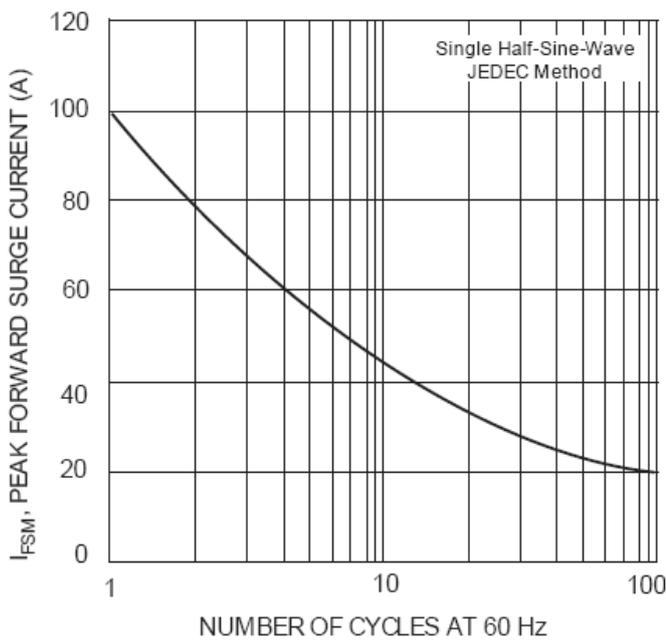


Fig. 3 Forward Surge Current Derating Curve

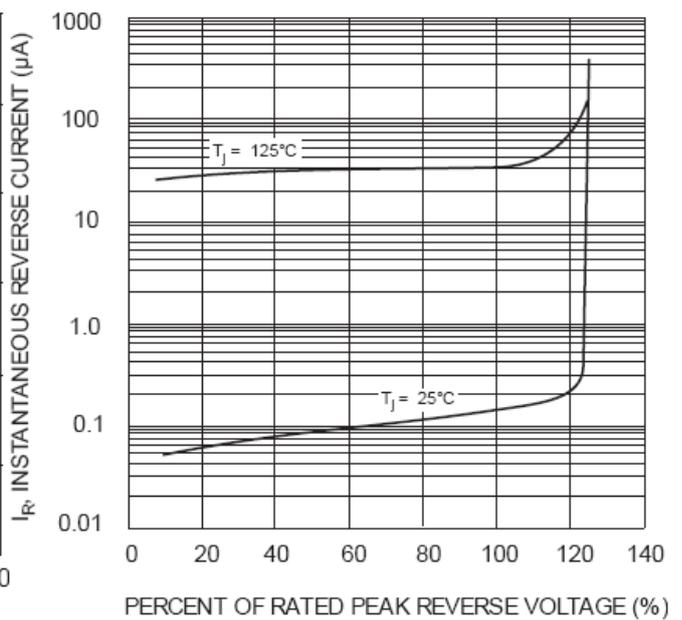


Fig. 4 Typical Reverse Characteristics



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Technical Data
Data Sheet N0563, Rev. A

Green Products

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